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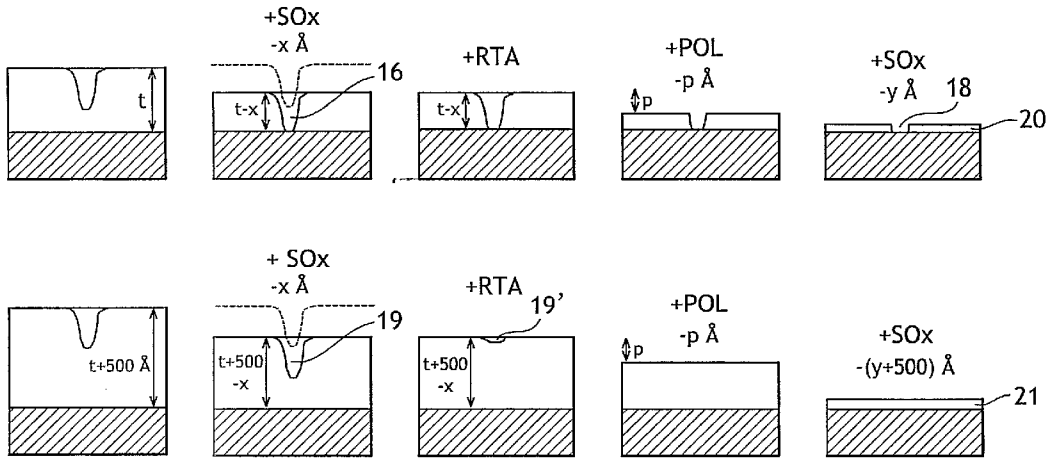
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(54) Title: METHOD FOR OBTAINING A THIN LAYER HAVING A LOW DENSITY OF HOLES



(57) Abstract: The invention proposes a method for determining the thickness of a part of a donor substrate which is to be transferred onto a support substrate, said part being intended to be thereafter submitted to a selected finishing sequence comprising at least one operation, the method being characterized in that a minimum thickness to be transferred is determined for said transferred part: to present, after each operation of the finishing sequence, a density of killing holes less than said maximal density, and to reach said selected thickness once the complete finishing sequence achieved.

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